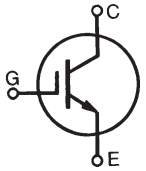
IXYS

High Voltage IGBT
For Capacitor Discharge Applications

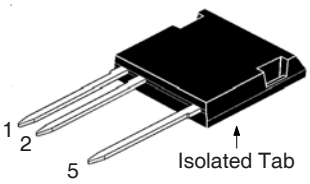
IXGF36N300

V_{CES} = 3000V
I_{C25} = 36A
$V_{CE(sat)}$ ≤ 2.7V



(Electrically Isolated Tab)

ISOPLUS i4-Pak™



1 = Gate 5 = Collector
2 = Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	T_C = 25°C	36	A
I_{C110}	T_C = 110°C	18	A
I_{CM}	T_C = 25°C, V_{GE} = 20V, 1ms	400	A
SSOA	V_{GE} = 20V, T_{VJ} = 125°C, R_G = 2Ω	I_{CM} = 300	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \bullet V_{CES}$	
P_C	T_C = 25°C	160	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
F_C	Mounting Force	20..120/4.5..27	Nm/lb-in.
V_{ISOL}	50/60Hz, 1 minute	4000	V~
Weight		5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	3000			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}, V_{GE} = 0V			50	μA
	Note 2 ,T_J = 125°C			2	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±200	nA
$V_{CE(sat)}$	I_C = 36A, V_{GE} = 15V, Note 1			2.7	V
	I_C = 100A			5.2	V

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V Electrical Isolation
- High Peak Current Capability
- Low Saturation Voltage
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Applications

- Capacitor Discharge
- Pulser Circuits

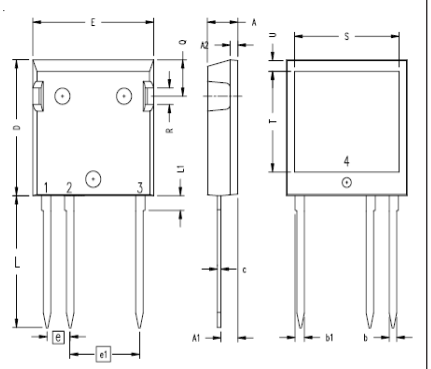
Advantages

- High Power Density
- Easy to Mount

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	I_C = 36A, V_{CE} = 10V, Note 1	15	25	S
$I_{C(ON)}$	V_{GE} = 15V, V_{CE} = 20V, Note 1		360	A
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		2690	pF
C_{oes}			123	pF
C_{res}			34	pF
Q_g	I_C = 30A, V_{GE} = 15V, V_{CE} = 600V		136	nC
Q_{ge}			21	nC
Q_{gc}			52	nC
$t_{d(on)}$	**Resistive Switching Times**		36	ns
t_r	I_C = 36A, V_{GE} = 15V		185	ns
$t_{d(off)}$	V_{CE} = 1500V, R_G = 2Ω		215	ns
t_f			540	ns
R_{thJC}				0.78 °C/W
R_{thCS}			0.15	°C/W
R_{thJA}			30	°C/W

ISOPLUS i4-Pak™ (HV) Outline





Pin 1 = Gate
Pin 2 = Emitter
Pin 3 = Collector
Tab 4 = Isolated

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Notes:

1. Pulse test, t < 300μs, duty cycle, d < 2%.
2. Device must be heatsunk for high-temperature leakage current measurements to avoid thermal runaway.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

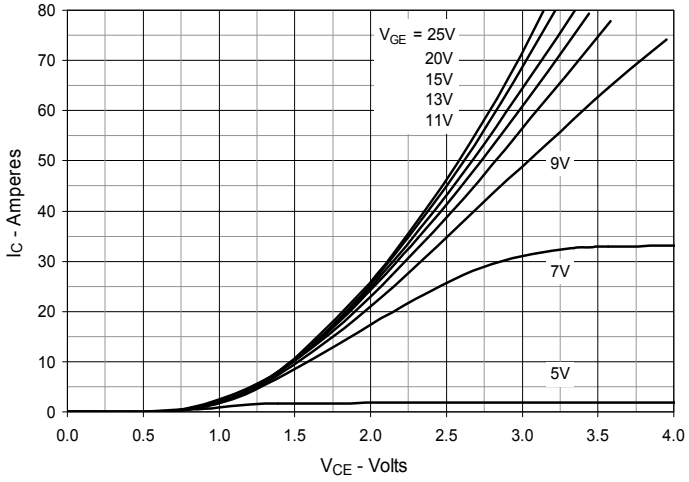


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

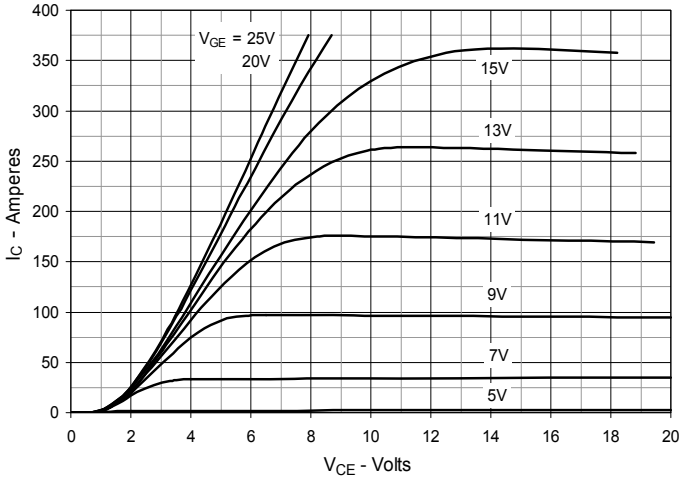


Fig. 3. Output Characteristics @ T_J = 125ºC

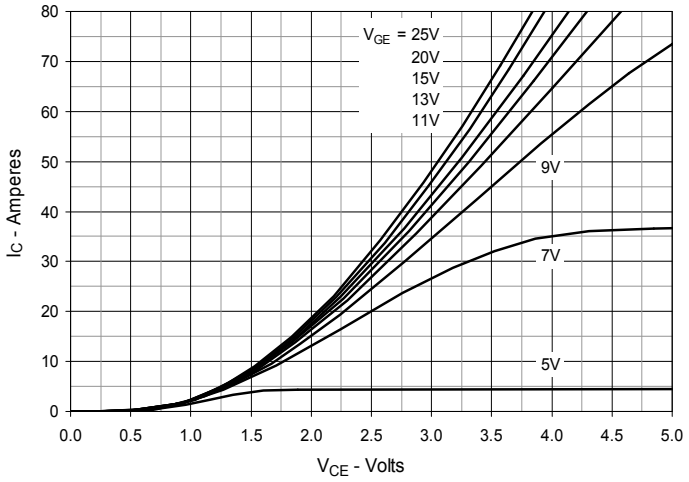


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

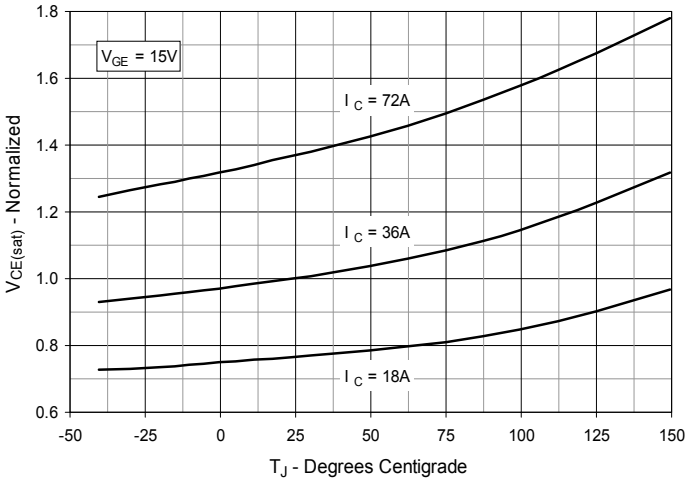


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

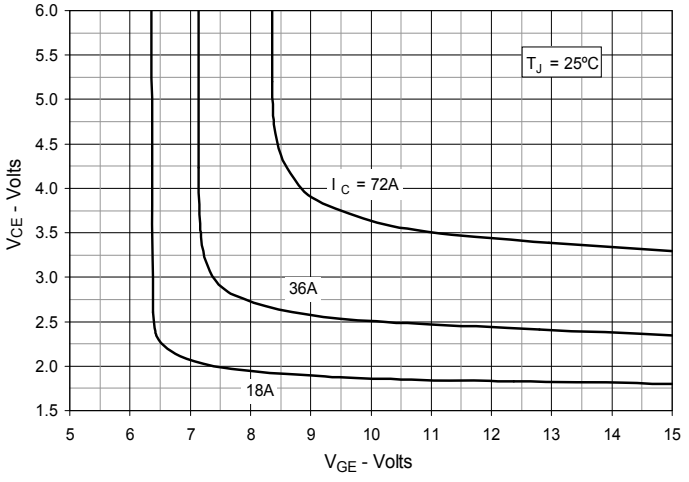
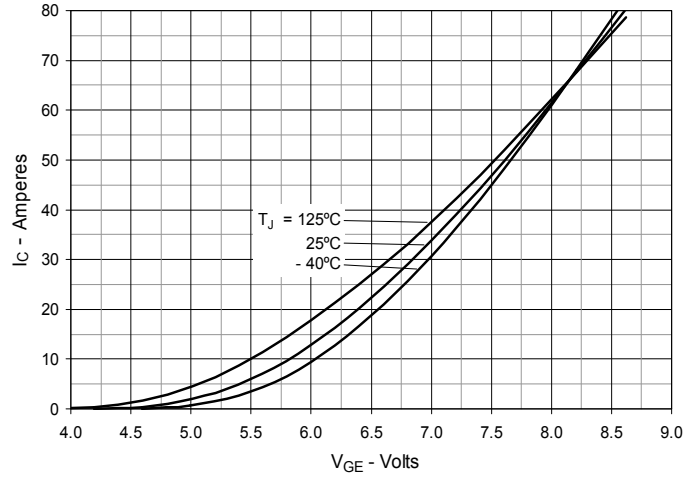


Fig. 6. Input Admittance



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Fig. 7. Transconductance

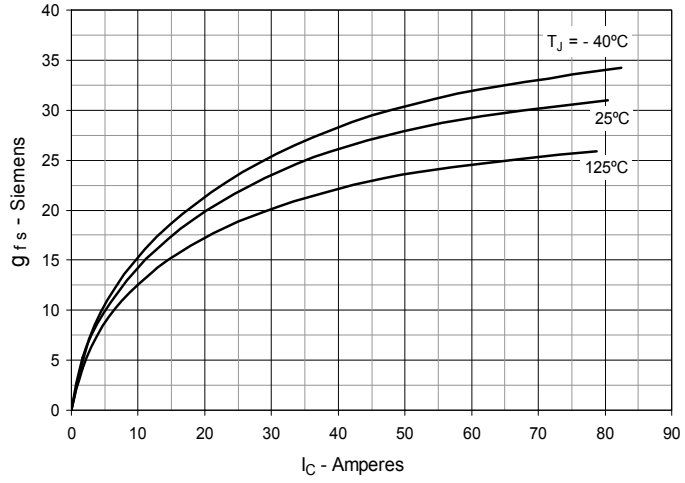


Fig. 8. Gate Charge

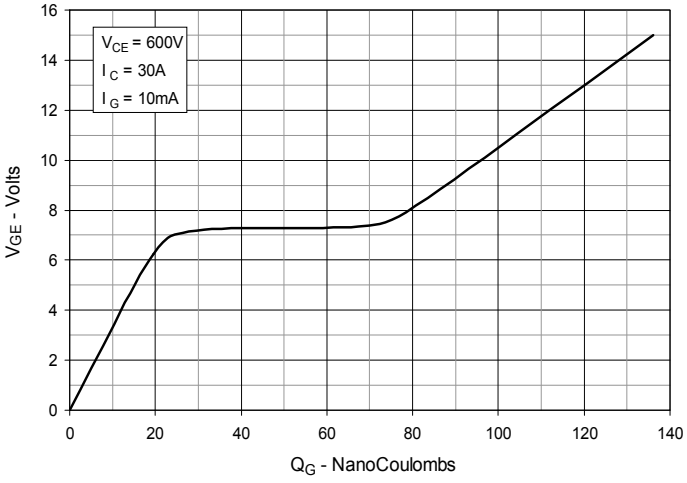


Fig. 9. Reverse-Bias Safe Operating Area

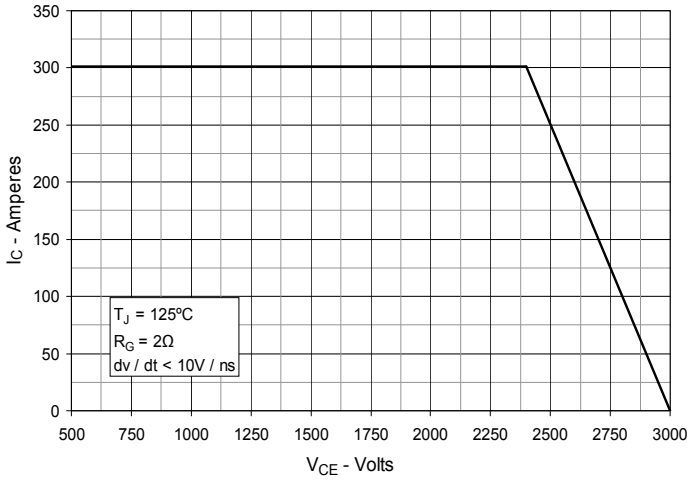


Fig. 10. Capacitance

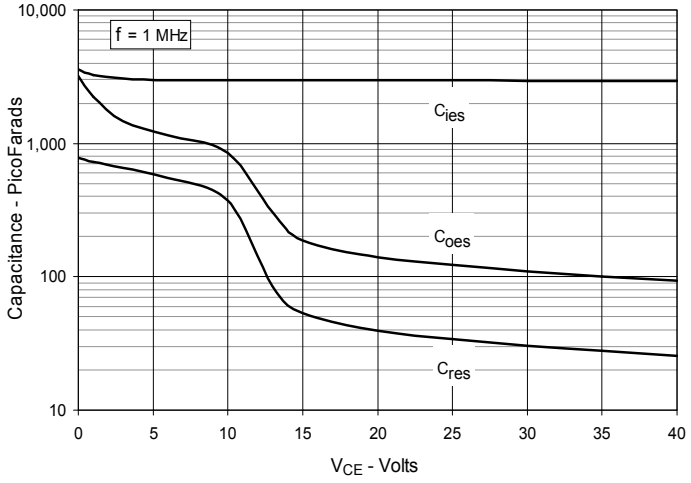
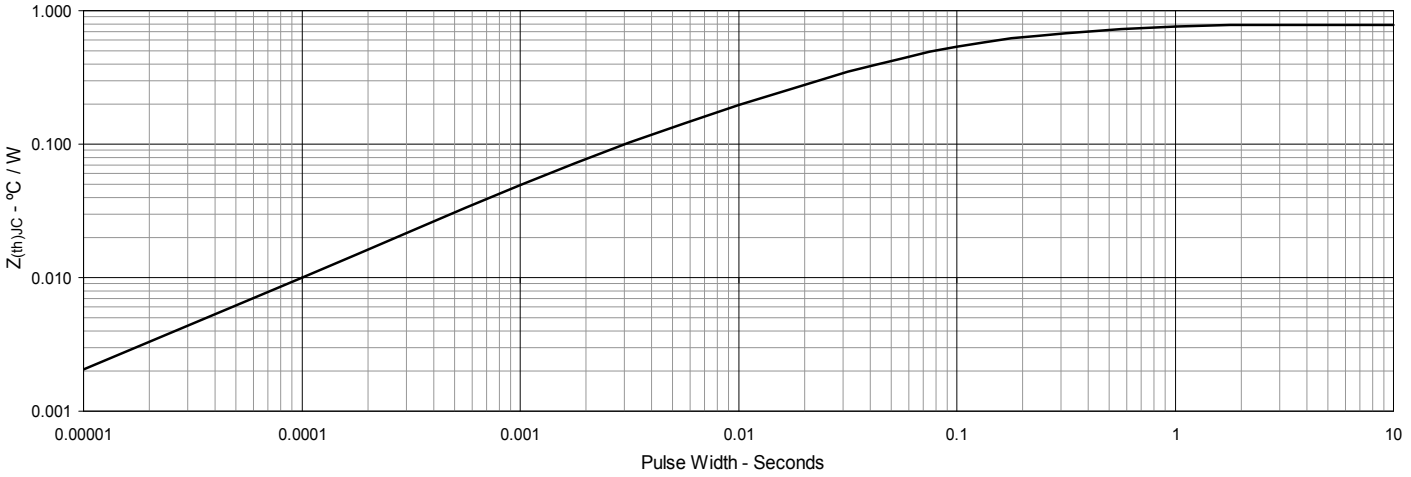


Fig. 11. Maximum Transient Thermal Impedance



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Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

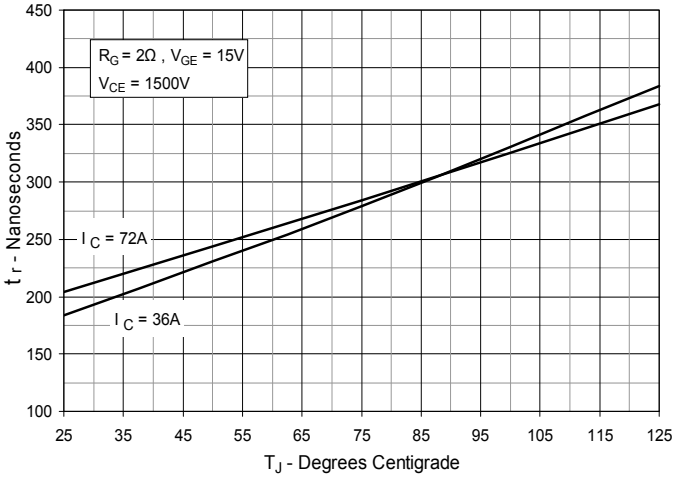


Fig. 13. Resistive Turn-on Rise Time vs. Drain Current

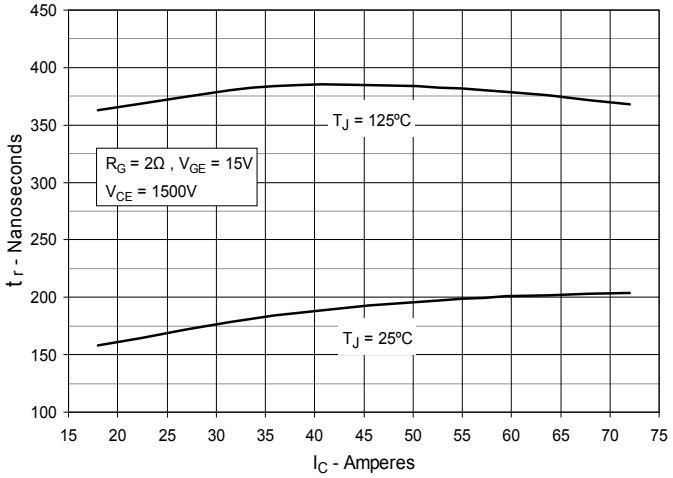


Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

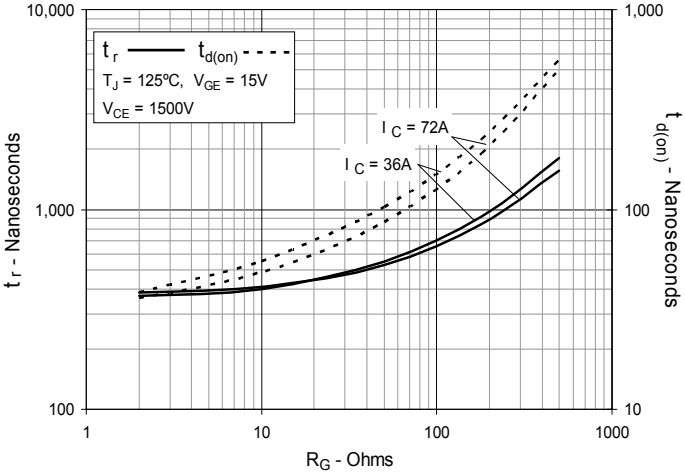


Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

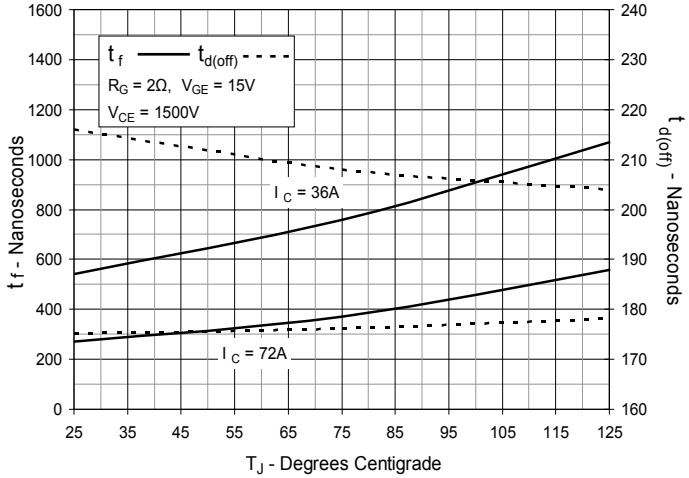


Fig. 16. Resistive Turn-off Switching Times vs. Drain Current

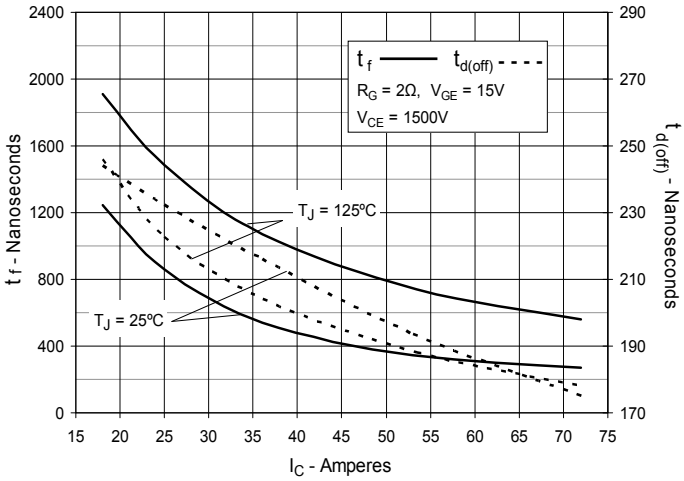
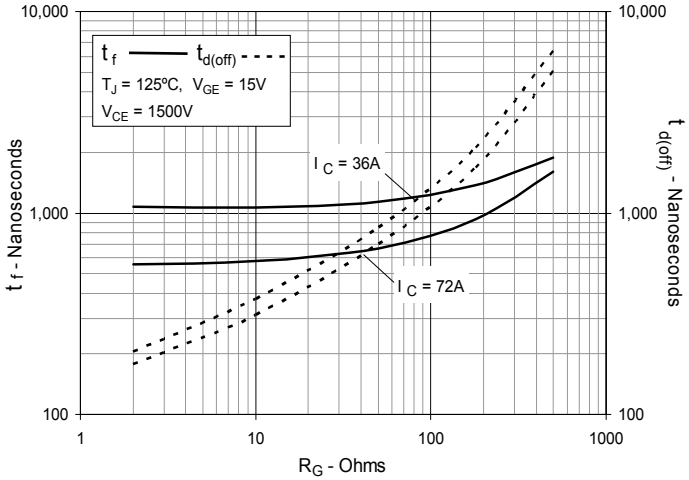


Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance



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